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Thien F.

TESPONSE S113/03 agg

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

n re Application of:)	
Hisao HAYASHI et al)	Group Art Unit:
)	*
Application No.: 09/772,986)	Examiner: Tran,
•)	
Filed: January 31, 2001)	
)	
For: THIN FILM SEMICONDUCTOR)	
DEVICE, DISPLAY DEVICE USING)	
SUCH THIN FILM SEMICONDUCTOR)	
DEVICE AND MANUFACTURING)	
METHOD THEREOF)	

BOX NON-FEE AMENDMENT Commissioner of Patents Washington, D.C. 20231 RECEIVED

RESPONSE TO OFFICE ACTION

Sir:

Responsive to the non-final Office Action dated February 7, 2003, (Paper No. 14), please consider the following remarks.

<u>REMARKS</u>

Applicant is in receipt of the detailed Office Action mailed February 7, 2003. Claims 1-8 and 13-16 are rejected. Applicant requests reconsideration of the remaining claims in view of the following remarks.

35 USC § 103 Rejection

The Examiner rejects Claims 1-8 and 13-16 under 35 USC §103 as being unpatentable over Hisao et al (JP 10209467). The Examiner states that the disclosed range for the gate insulating film and the gate electrode can yield a thickness of the gate insulating film that is thicker than the gate electrode. In essence, the Examiner states that the overlapping ranges in the cited reference create a *prima facie* case of obviousness. Applicant traverses the rejection. Accordingly, MPEP 2144.05 states: